

2SK3159

Silicon N Channel MOS FET
High Speed Power Switching

REJ03G1084-0400

Rev.4.00

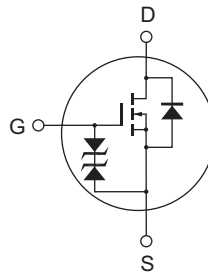
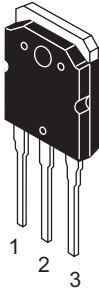
May 15, 2006

Features

- Low on-resistance
 $R_{DS} = 23 \text{ m}\Omega$ typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

Outline

RENESAS Package code: PRSS0004ZE-A
(Package name: TO-3P)



1. Gate
2. Drain
(Flange)
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	150	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	50	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	200	A
Body-drain diode reverse drain current	I_{DR}	50	A
Avalanche current	I_{AP} ^{Note3}	50	A
Avalanche energy	E_{AR} ^{Note3}	187	mJ
Channel dissipation	P_{ch} ^{Note2}	125	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Notes: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$ 2. Value at $T_c = 25^\circ C$ 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50\ \Omega$

Electrical Characteristics

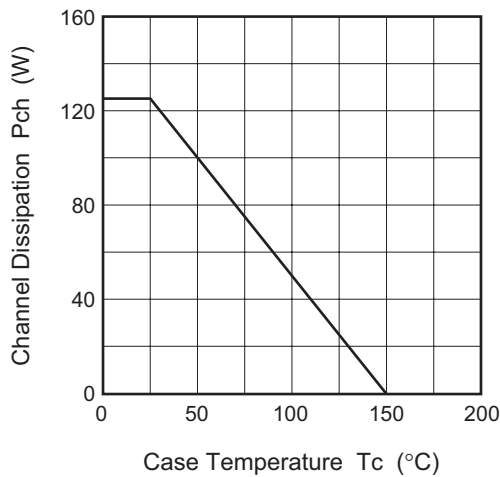
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	150	—	—	V	$I_D = 10\text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\ \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16\text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 150\text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$I_D = 1\text{ mA}$, $V_{DS} = 10\text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	23	30	mΩ	$I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	28	42	mΩ	$I_D = 25\text{ A}$, $V_{GS} = 4\text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	27	45	—	S	$I_D = 25\text{ A}$, $V_{DS} = 10\text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	4000	—	pF	$V_{DS} = 10\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$
Output capacitance	C_{oss}	—	1650	—	pF	
Reverse transfer capacitance	C_{rss}	—	590	—	pF	
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = 25\text{ A}$, $V_{GS} = 10\text{ V}$, $R_L = 1.2\ \Omega$
Rise time	t_r	—	280	—	ns	
Turn-off delay time	$t_{d(off)}$	—	830	—	ns	
Fall time	t_f	—	450	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.95	—	V	$I_F = 50\text{ A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	200	—	ns	$I_F = 50\text{ A}$, $V_{GS} = 0$ $di_F/dt = 50\text{ A}/\mu s$

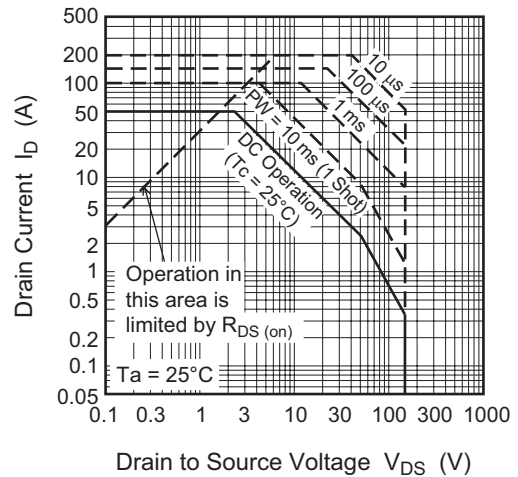
Note: 4. Pulse test

Main Characteristics

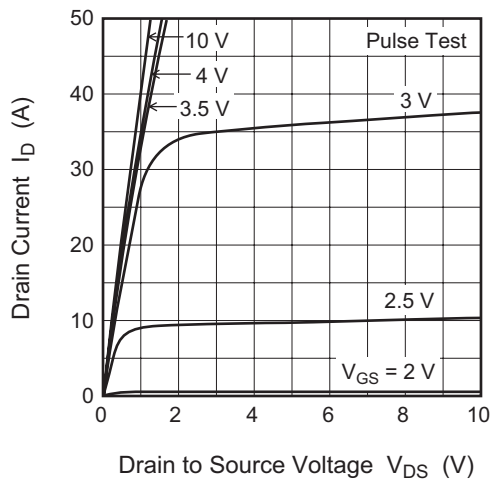
Power vs. Temperature Derating



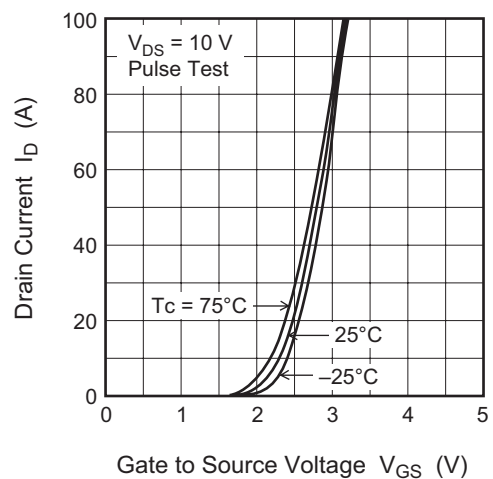
Maximum Safe Operation Area



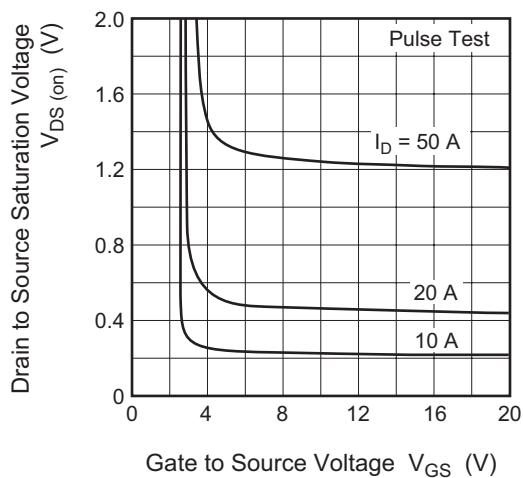
Typical Output Characteristics



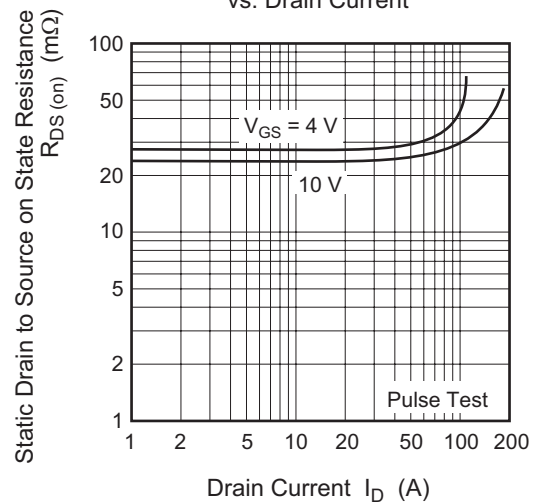
Typical Transfer Characteristics



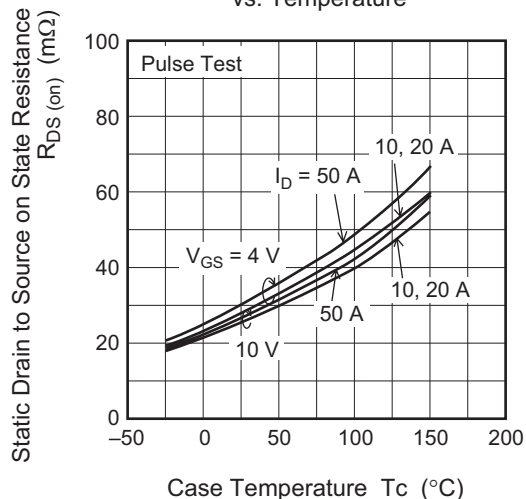
Drain to Source Saturation Voltage vs. Gate to Source Voltage



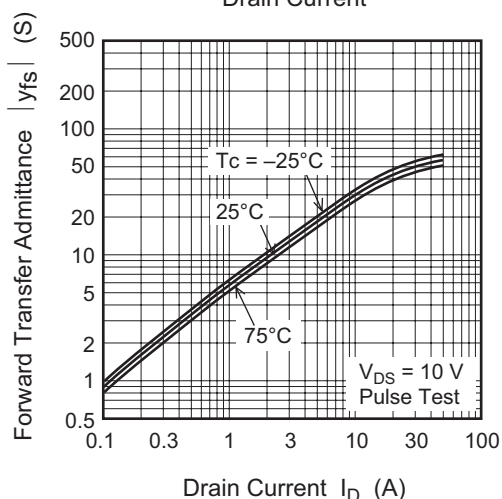
Static Drain to Source on State Resistance vs. Drain Current



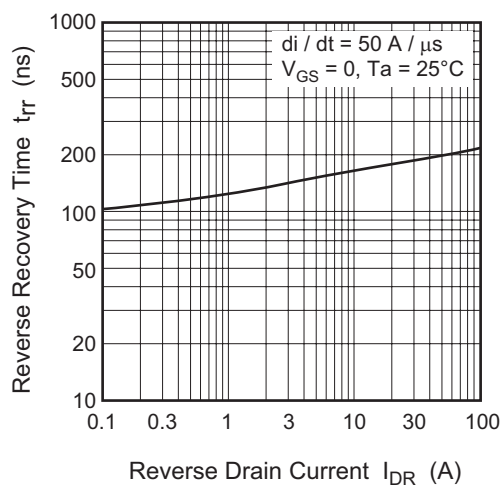
Static Drain to Source on State Resistance vs. Temperature



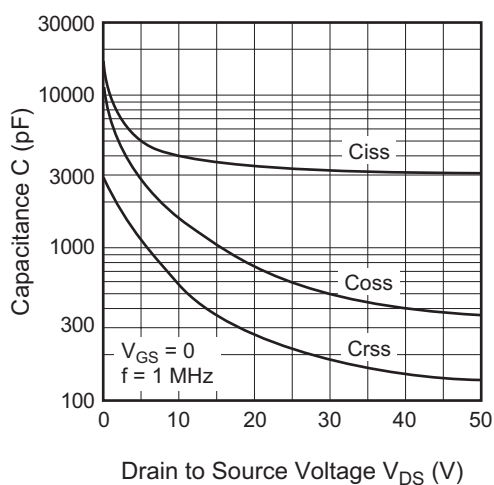
Forward Transfer Admittance vs. Drain Current



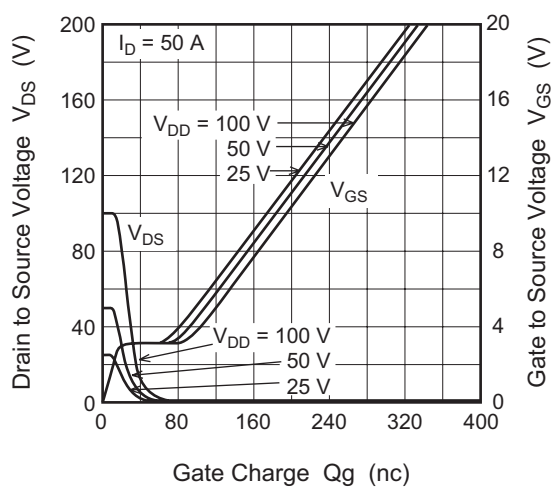
Body to Drain Diode Reverse Recovery Time



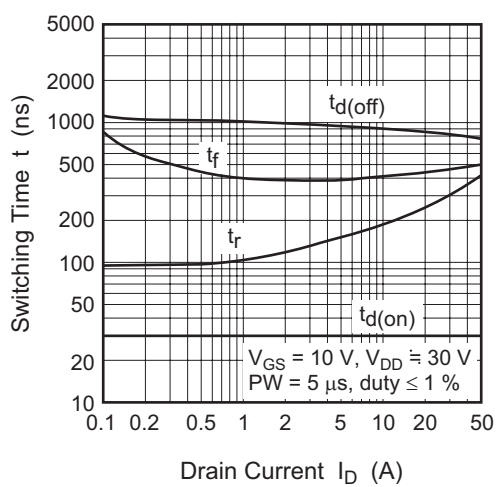
Typical Capacitance vs. Drain to Source Voltage

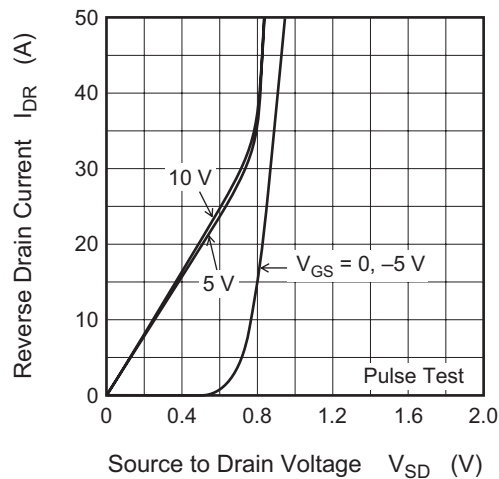
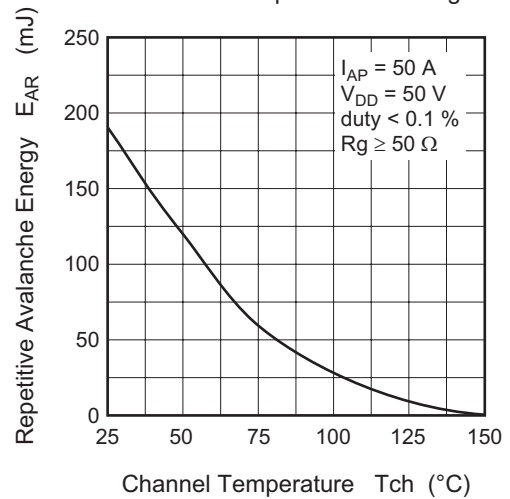


Dynamic Input Characteristics

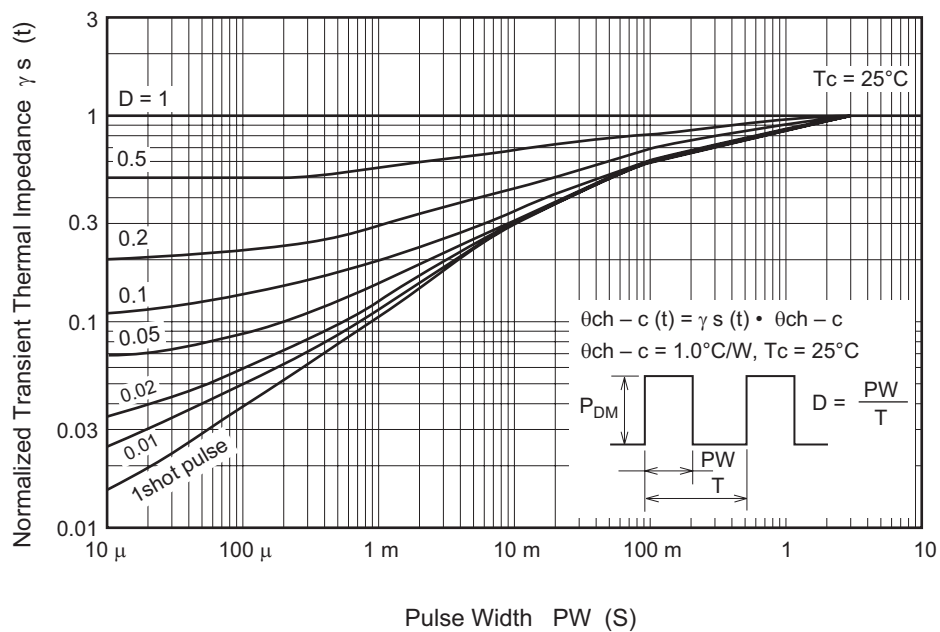


Switching Characteristics

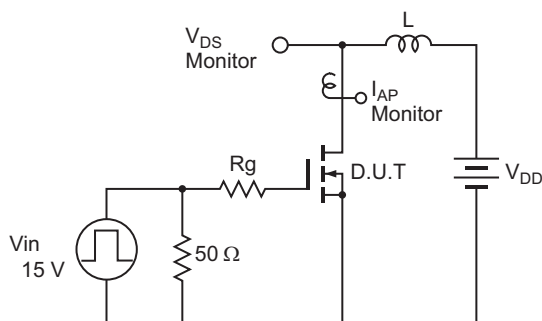


Reverse Drain Current vs.
Source to Drain VoltageMaximum Avalanche Energy vs.
Channel Temperature Derating

Normalized Transient Thermal Impedance vs. Pulse Width

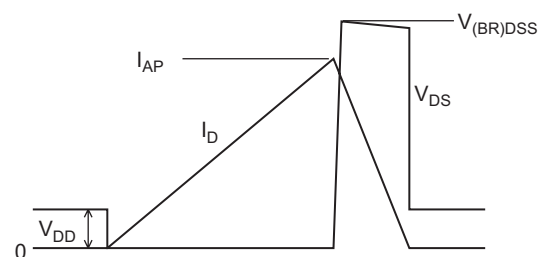


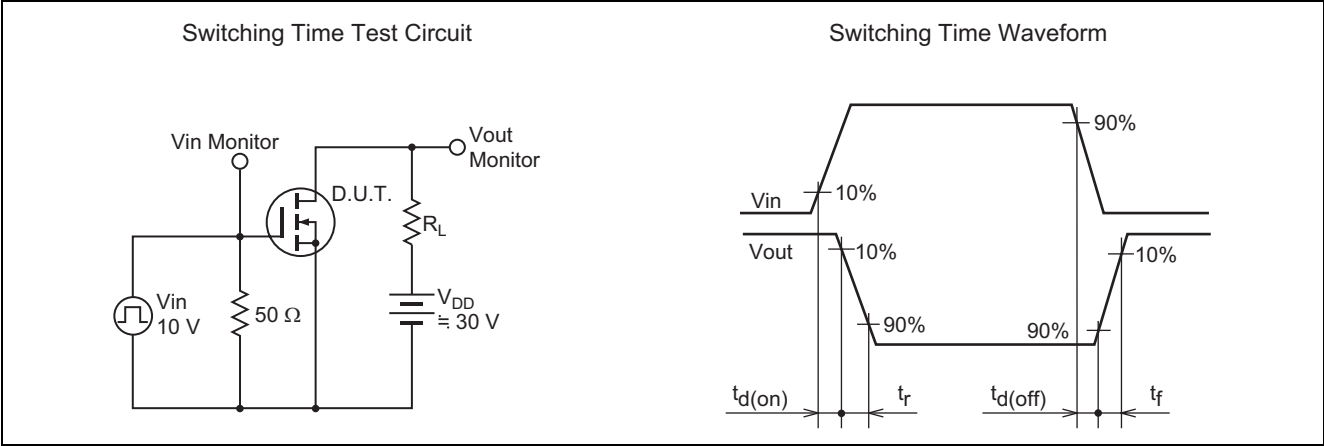
Avalanche Test Circuit



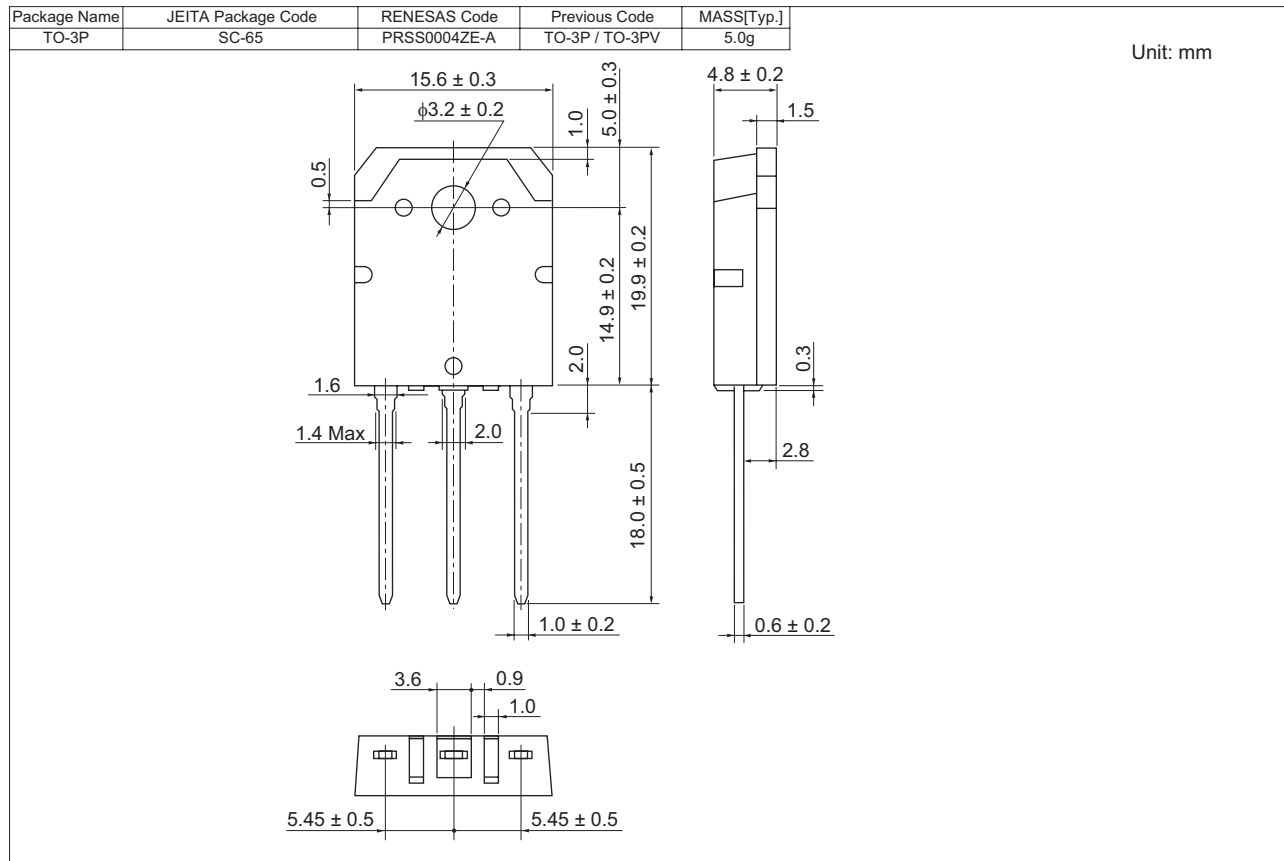
Avalanche Waveform

$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK3159-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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